Yong Seung Kim

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/11300109/publications.pdf

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		567281	888059
19	1,688	15	17
papers	citations	h-index	g-index
10	10	10	22.42
19	19	19	3243
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Thickness-Independent Transport Channels in Topological Insulator <mml:math display="inline" xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>Bi</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi 109,="" 116804.<="" 2012,="" films.="" letters,="" physical="" review="" td=""><td>>Se^{:8}mml</td><td>:m306 :mi><mml:rn< td=""></mml:rn<></td></mml:mi></mml:msub></mml:math>	>Se ^{:8} mml	:m306 :mi> <mml:rn< td=""></mml:rn<>
2	Bright visible light emission from graphene. Nature Nanotechnology, 2015, 10, 676-681.	31.5	284
3	Bi <mml:mathxmlns:mml="http: 1998="" math="" mathml"<br="" www.w3.org="">display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:mrow </mml:msub>Se<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow< td=""><td>3.2</td><td>270</td></mml:mrow<></mml:msub></mml:math </mml:mathxmlns:mml="http:>	3.2	270
4	Is small map 3 s/mml; map s/mml; msubs s/mml; maths. Physical Review B, 2011, 84, . Epitaxial growth of topological insulator Bi2Se3 film on Si(111) with atomically sharp interface. Thin Solid Films, 2011, 520, 224-229.	1.8	180
5	Methane as an effective hydrogen source for single-layer graphene synthesis on Cu foil by plasma enhanced chemical vapor deposition. Nanoscale, 2013, 5, 1221.	5.6	104
6	Spin valve effect of NiFe/graphene/NiFe junctions. Nano Research, 2013, 6, 373-380.	10.4	79
7	Focused-Laser-Enabled p–n Junctions in Graphene Field-Effect Transistors. ACS Nano, 2013, 7, 5850-5857.	14.6	76
8	Surface versus bulk state in topological insulator Bi2Se3 under environmental disorder. Applied Physics Letters, 2011, 99, .	3.3	73
9	Direct growth of patterned graphene on SiO ₂ substrates without the use of catalysts or lithography. Nanoscale, 2014, 6, 10100-10105.	5 . 6	66
10	Ordered growth of topological insulator Bi2Se3 thin films on dielectric amorphous SiO2 by MBE. Nanoscale, 2013, 5, 10618.	5. 6	64
11	Electromagnetic Saturation of Angstrom-Sized Quantum Barriers at Terahertz Frequencies. Physical Review Letters, 2015, 115, 125501.	7.8	60
12	Direct Integration of Polycrystalline Graphene into Light Emitting Diodes by Plasma-Assisted Metal-Catalyst-Free Synthesis. ACS Nano, 2014, 8, 2230-2236.	14.6	55
13	Polarized Raman spectroscopy with differing angles of laser incidence on single-layer graphene. Nanoscale Research Letters, 2015, 10, 45.	5.7	20
14	Tunnelling current-voltage characteristics of Angstrom gaps measured with terahertz time-domain spectroscopy. Scientific Reports, 2016, 6, 29103.	3.3	18
15	Colossal Terahertz Nonlinearity in Angstrom- and Nanometer-Sized Gaps. ACS Photonics, 2016, 3, 1440-1445.	6.6	18
16	Universality of periodicity as revealed from interlayer-mediated cracks. Scientific Reports, 2017, 7, 43400.	3.3	8
17	Graphene film growth on sputtered thin Cu–Ni alloy film by inductively coupled plasma chemical vapor deposition. RSC Advances, 2014, 4, 63349-63353.	3 . 6	6
18	Terahertz funneling-induced quantum tunneling at angstrom scale. , 2016, , .		1

ARTICLE IF CITATIONS

19 Terahertz Quantum Plasmonics at Angstrom Scale., 2016,,... o